

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
-60V	45mΩ@-10V	-25A

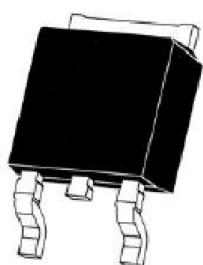
## Feature

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation
- Suffix "-Q1" for AEC-Q101

## Application

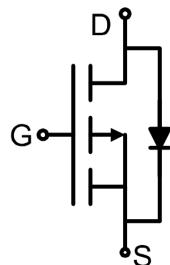
- High side switch for full bridge converter
- DC/DC converters for LCD display

## Package

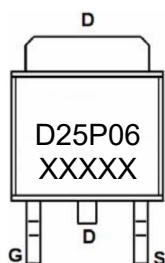


TO-252AB

## Circuit diagram



## Marking



**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-60	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	-25	A
Pulsed Drain Current	I <sub>DM</sub>	-60	A
Power Dissipation	P <sub>D</sub>	90	W
Thermal Resistance,Junction-to-Case	R <sub>θJC</sub>	1.4	°C/W
Single pulse avalanche energy	E <sub>AS</sub>	300	mJ
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

**Electrical characteristics (T<sub>A</sub>=25 °C, unless otherwise noted)**

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-60			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V			-1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-2		-3.5	V
Drain-source on-resistance <sup>1)</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -20A		37	45	mΩ
Forward transconductance <sup>1)</sup>	g <sub>FS</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -10A		25		S
<b>Dynamic characteristics<sup>2)</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V, f = 1MHz		3430		pF
Output Capacitance	C <sub>oss</sub>			391		
Reverse Transfer Capacitance	C <sub>rss</sub>			272		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = -10V, ID = -20A		46		nC
Gate-Source Charge	Q <sub>gs</sub>			9.5		
Gate-Drain Charge	Q <sub>gd</sub>			10.5		
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = -30V, V <sub>GS</sub> = -10V, R <sub>L</sub> = 1.5Ω, R <sub>GEN</sub> = 3Ω		12		nS
Turn-on rise time	t <sub>r</sub>			15		
Turn-off delay time	t <sub>d(off)</sub>			38		
Turn-off fall time	t <sub>f</sub>			15		
<b>Source-Drain Diode characteristics</b>						
Diode Forward Current <sup>1)</sup>	I <sub>S</sub>				-25	A
Diode Forward voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = -10A			-1.2	V
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, IF = -10A di/dt = 100A/μs <sup>1)</sup>		47		nS
Reverse Recovery Charge	Q <sub>rr</sub>			53		nC

Notes:

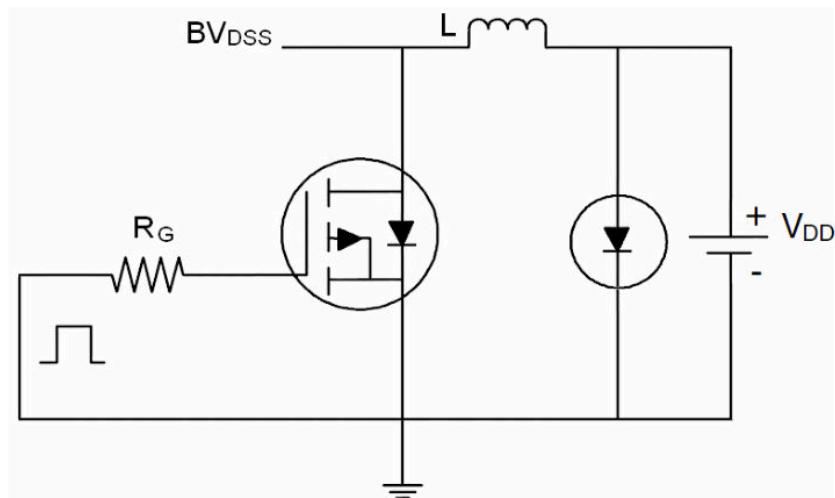
1) Pulse Test: Pulse Width &lt; 300μs, Duty Cycle ≤2%.

2) Guaranteed by design, not subject to production testing.

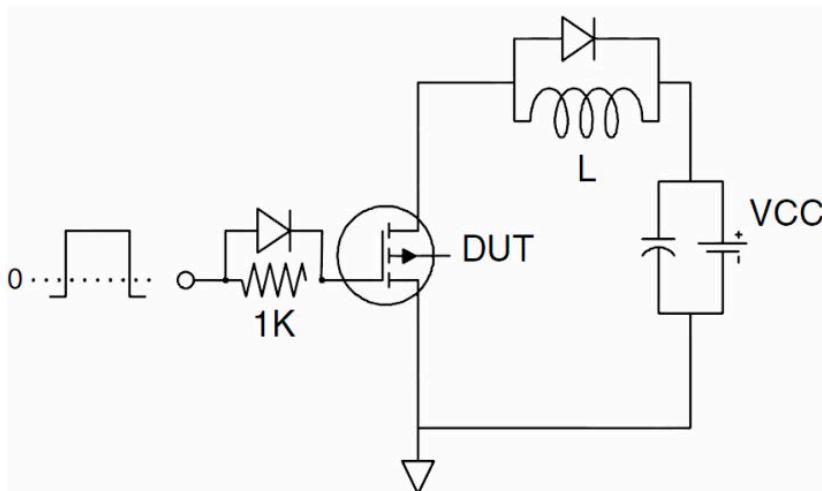


## Test Circuit

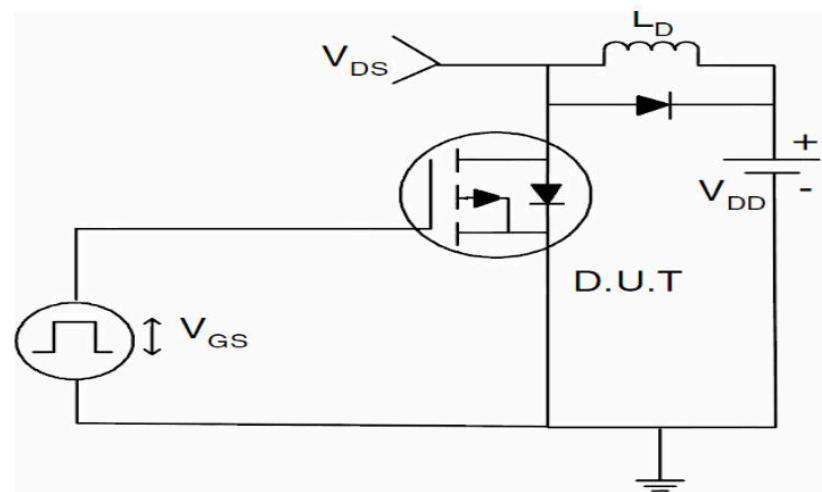
### 1) E<sub>AS</sub> test Circuit



### 2) Gate charge test Circuit



### 3) Switch Time Test Circuit



## Typical Characteristics

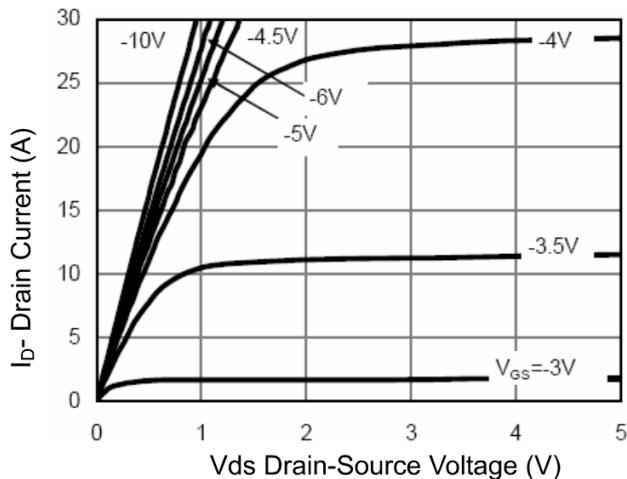


Figure 1 Output Characteristics

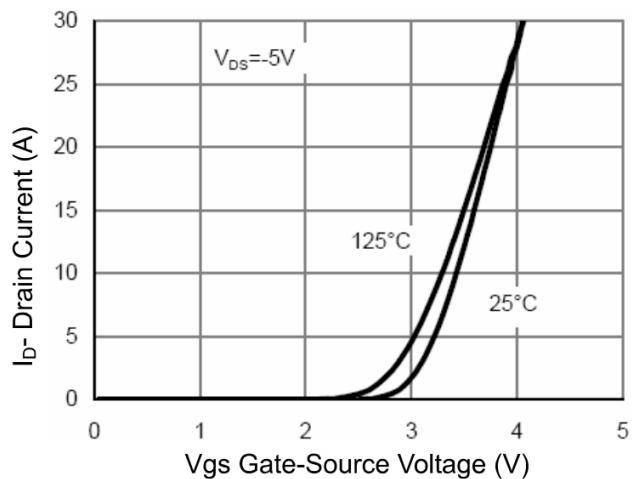


Figure 2 Transfer Characteristics

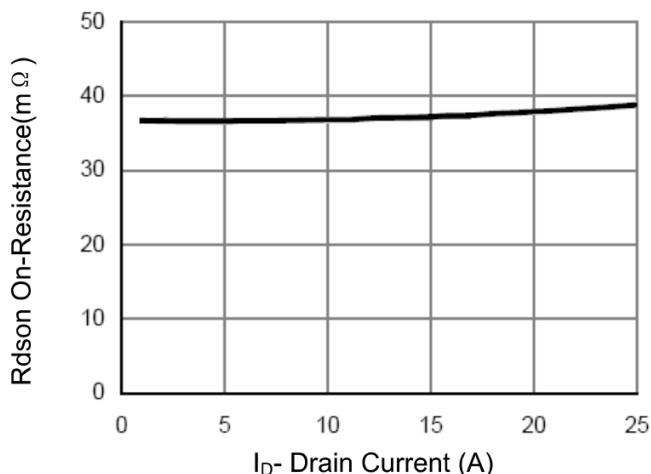


Figure 3 Rdson- Drain Current

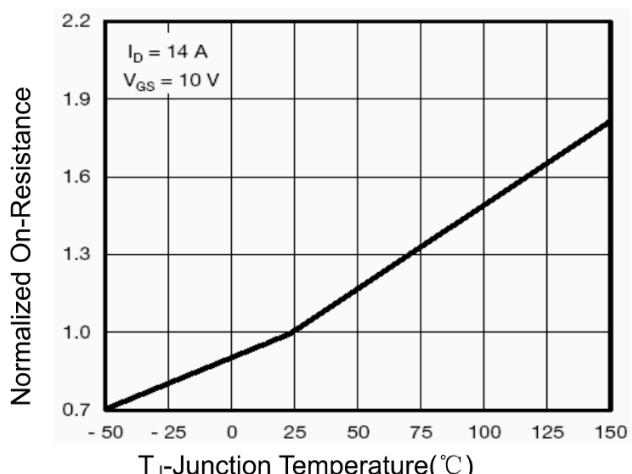


Figure 4 Rdson-Junction Temperature

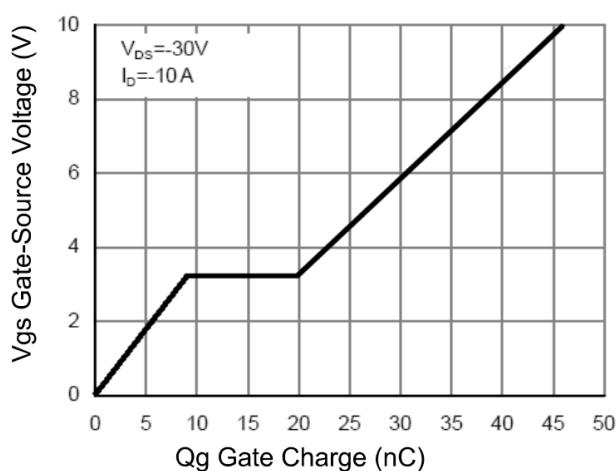


Figure 5 Gate Charge

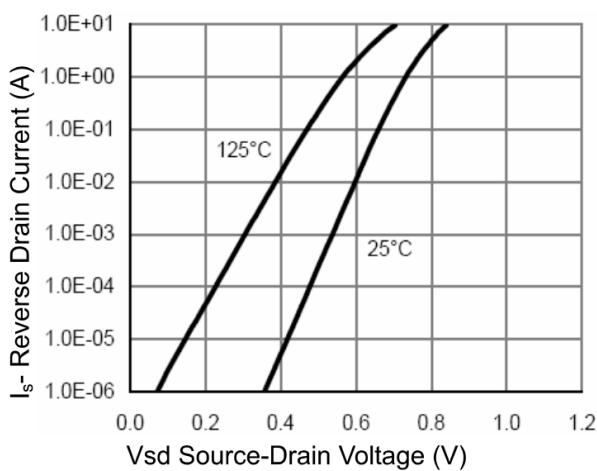
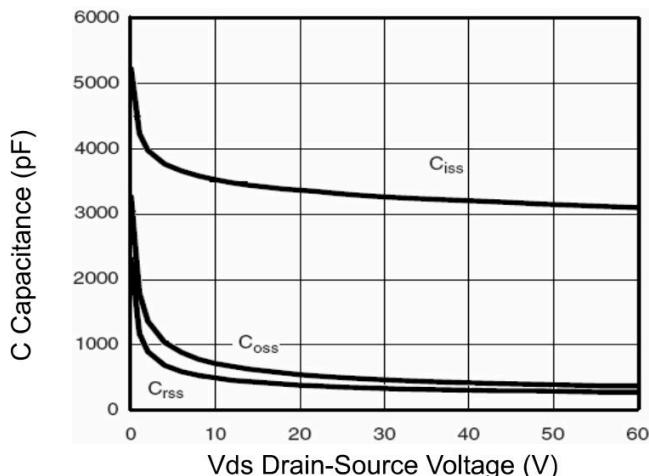
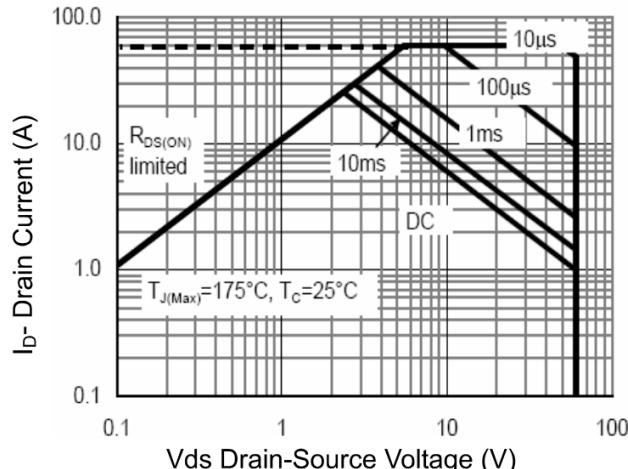


Figure 6 Source- Drain Diode Forward

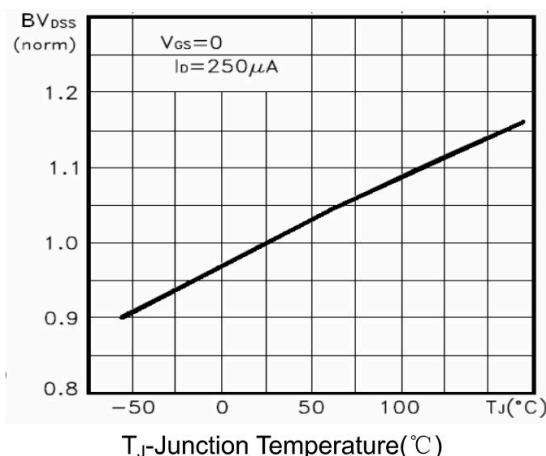
### Typical Characteristics



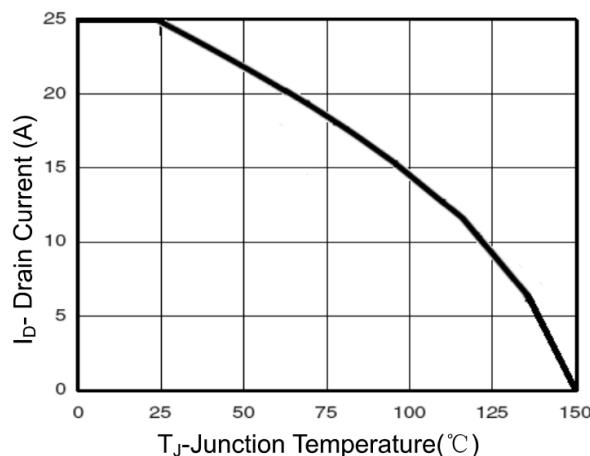
**Figure 7 Capacitance vs Vds**



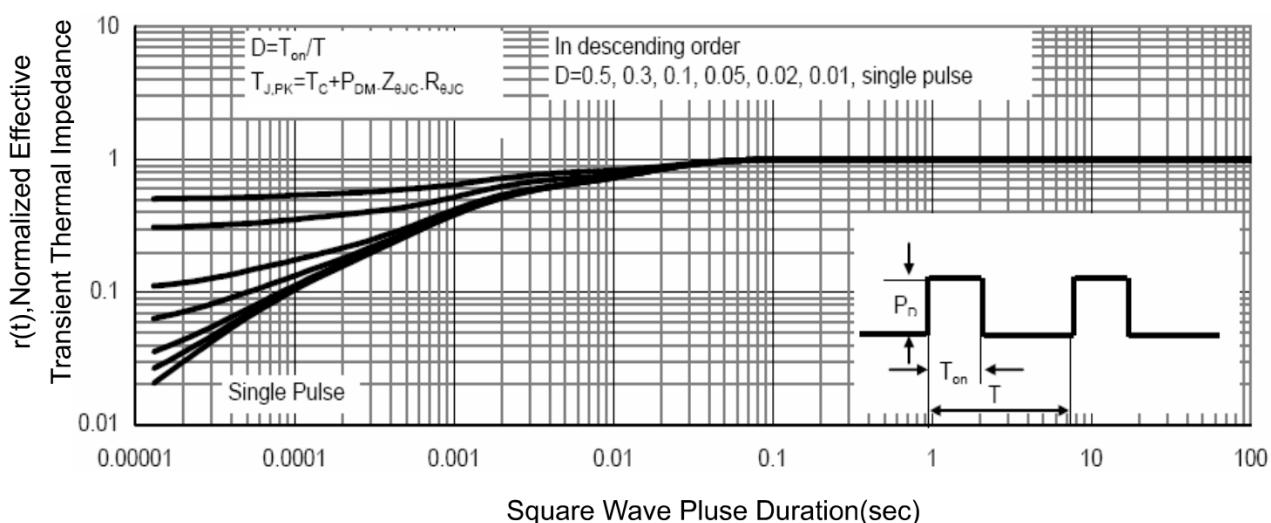
**Figure 8 Safe Operation Area**



**Figure 9  $BV_{DSS}$  vs Junction Temperature**

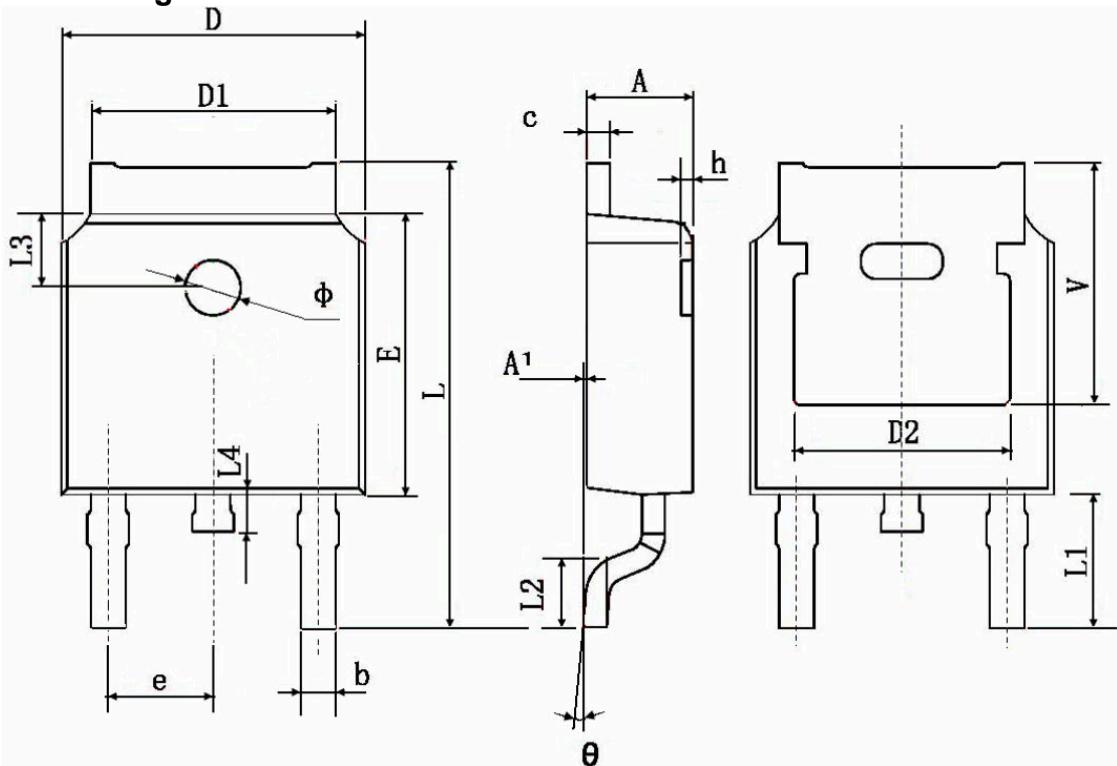


**Figure 10 ID Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## TO-252AB Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
$\Phi$	1.100	1.300	0.043	0.051
$\theta$	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	